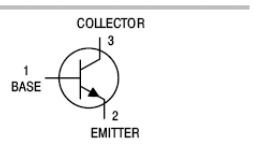
Silicon Epitaxial Planar Transistor **SS8050W**

FEATURES

Lead-free

- Collector Current.(I_C= 1.5A)
- Complementary To SS8550W.
- Collector dissipation:P_C=200mW(T_C=25℃)





SOT-323

APPLICATIONS

- High Collector Current.

ORDERING INFORMATION

Type No.	Marking	Package Code
SS8050W	Y1	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Dissipation	200	mW
T_j,T_{stg}	Junction and Storage Temperature	-55~150	℃

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=2mA,I_B=0	25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}=40V,I_E=0		0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=20V,I_B=0		0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0		0.1	μA

Silicon Epitaxial Planar Transistor **SS8050W**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
DC current gain	h_{FE}	V_{CE}=1V,I_C=100mA	120	400	
		V_{CE}=1V,I_C=800mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=800 mA, I_B= 80mA		0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=800 mA, I_B= 80mA		1.2	V
Base-emitter voltage	V_{BE}	V_{CE}=1V I_C=10mA		1	V
Transition frequency	f_T	V_{CE}=10V, I_C= 50mA f=30MHz	100		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

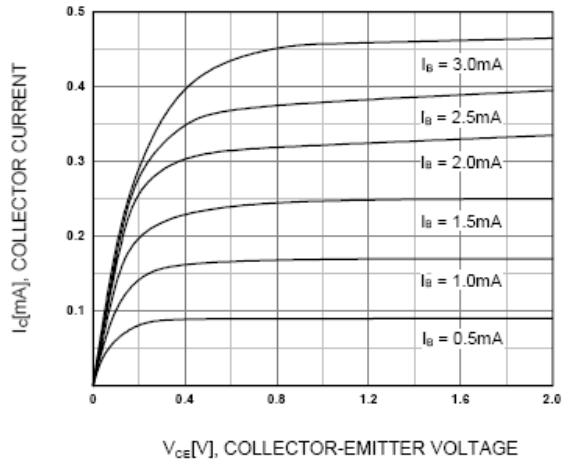


Figure 1. Static Characteristic

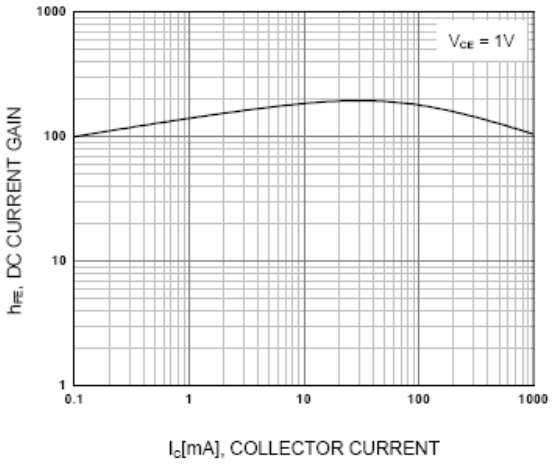


Figure 2. DC current Gain

Silicon Epitaxial Planar Transistor **SS8050W**

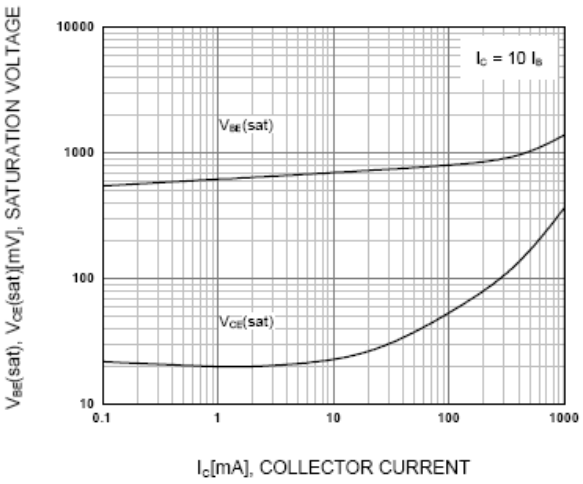


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

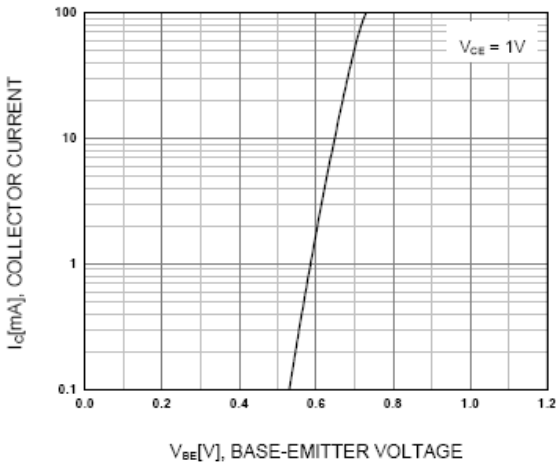


Figure 4. Base-Emitter On Voltage

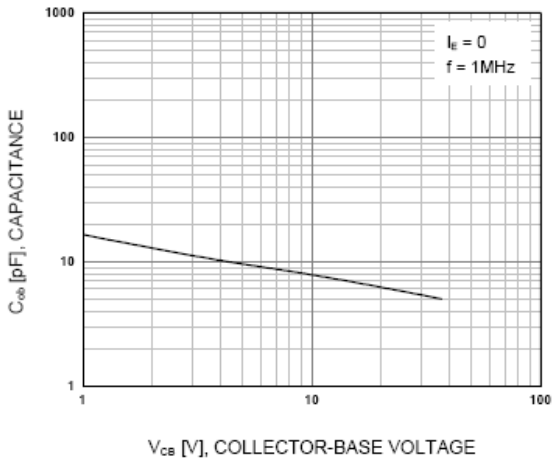


Figure 5. Collector Output Capacitance

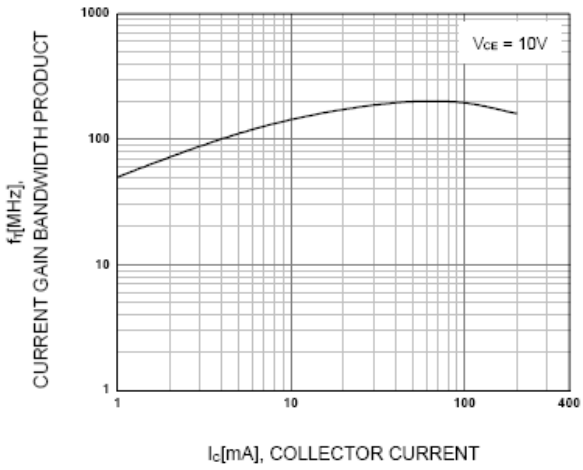
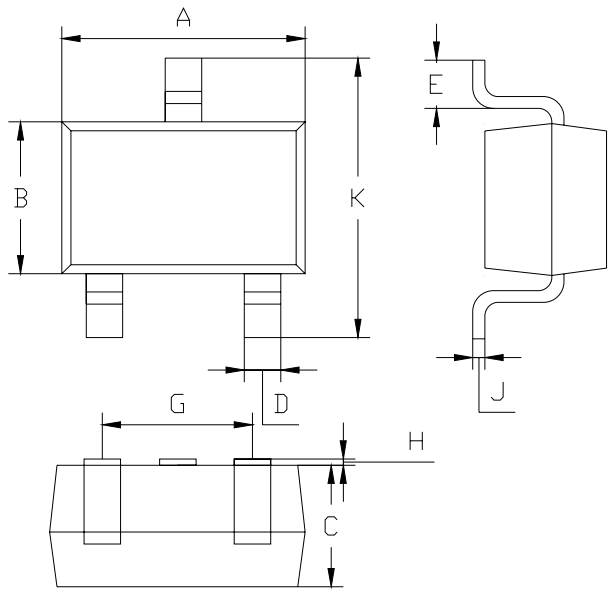


Figure 6. Current Gain Bandwidth Product

Silicon Epitaxial Planar Transistor **SS8050W**

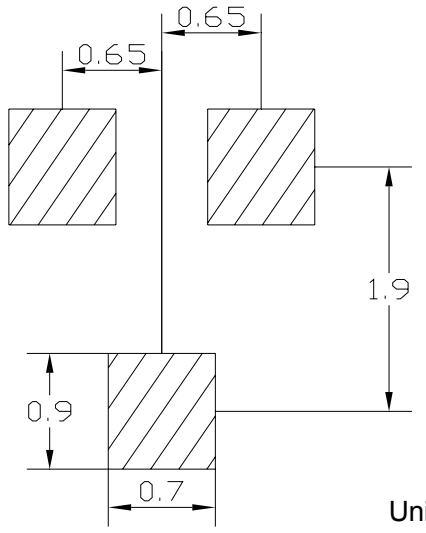
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.1	2.3
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
SS8050W	SOT-323	3000/Tape&Reel